



74AC245

OCTAL BUS TRANSCEIVER WITH 3 STATE OUTPUTS (NON INVERTED)

- HIGH SPEED: $t_{PD} = 4.5ns$ (TYP.) at $V_{CC} = 5V$
- LOW POWER DISSIPATION:
 $I_{CC} = 4\mu A$ (MAX.) at $T_A=25^\circ C$
- HIGH NOISE IMMUNITY:
 $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (MIN.)
- 50Ω TRANSMISSION LINE DRIVING CAPABILITY
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = I_{OL} = 24mA$ (MIN)
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \approx t_{PHL}$
- OPERATING VOLTAGE RANGE:
 V_{CC} (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 244
- IMPROVED LATCH-UP IMMUNITY



ORDER CODES

PACKAGE	TUBE	T & R
DIP	74AC245B	
SOP	74AC245M	74AC245MTR
TSSOP		74AC245TTR

DESCRIPTION

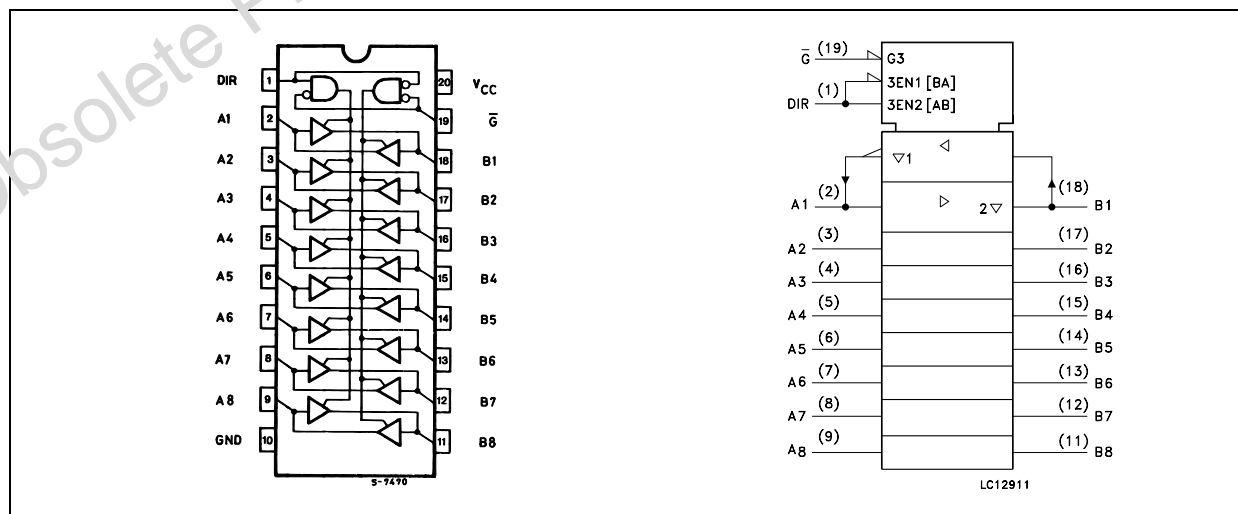
The 74AC245 is an advanced high-speed CMOS OCTAL BUS TRANSCEIVER (3-STATE) fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS technology. This IC is intended for two-way asynchronous communication between data buses and the direction of data transmission is determined by

DIR input. The enable input \bar{G} can be used to disable the device so that the buses are effectively isolated.

All floating bus terminals during HIGH-Z state must be held HIGH or LOW

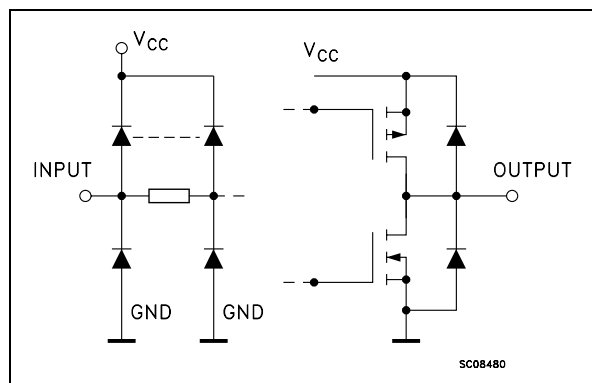
All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



74AC245

INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1	DIR	Directional Control
2, 3, 4, 5, 6, 7, 8, 9	A1 to A8	Data Inputs/Outputs
18, 17, 16, 15, 14, 13, 12, 11	B1 to B8	Data Inputs/Outputs
19	G	Output Enable Input
10	GND	Ground (0V)
20	V _{CC}	Positive Supply Voltage

TRUTH TABLE

INPUTS		FUNCTION		OUTPUT
\overline{G}	DIR	A BUS	B BUS	Y _n
L	L	OUTPUT	INPUT	A = B
L	H	INPUT	OUTPUT	B = A
H	X	Z	Z	Z

X : Don't Care

Z : High Impedance

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
V _I	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
I _O	DC Output Current	± 50	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 400	mA
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	2 to 6	V
V _I	Input Voltage	0 to V _{CC}	V
V _O	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time V _{CC} = 3.0, 4.5 or 5.5V (note 1)	8	ns/V

1) V_{IN} from 30% to 70% of V_{CC}

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V _{IH}	High Level Input Voltage	3.0	V _O = 0.1 V or V _{CC} -0.1V	2.1	1.5		2.1		2.1		V
		4.5		3.15	2.25		3.15		3.15		
		5.5		3.85	2.75		3.85		3.85		
V _{IL}	Low Level Input Voltage	3.0	V _O = 0.1 V or V _{CC} -0.1V		1.5	0.9		0.9		0.9	V
		4.5			2.25	1.35		1.35		1.35	
		5.5			2.75	1.65		1.65		1.65	
V _{OH}	High Level Output Voltage	3.0	I _O =-50 μA	2.9	2.99		2.9		2.9		V
		4.5	I _O =-50 μA	4.4	4.49		4.4		4.4		
		5.5	I _O =-50 μA	5.4	5.49		5.4		5.4		
		3.0	I _O =-12 mA	2.56			2.46		2.4		
		4.5	I _O =-24 mA	3.86			3.76		3.7		
		5.5	I _O =-24 mA	4.86			4.76		4.7		
V _{OL}	Low Level Output Voltage	3.0	I _O =50 μA		0.002	0.1		0.1		0.1	V
		4.5	I _O =50 μA		0.001	0.1		0.1		0.1	
		5.5	I _O =50 μA		0.001	0.1		0.1		0.1	
		3.0	I _O =12 mA			0.36		0.44		0.5	
		4.5	I _O =24 mA			0.36		0.44		0.5	
		5.5	I _O =24 mA			0.36		0.44		0.5	
I _I	Input Leakage Current	5.5	V _I = V _{CC} or GND			± 0.1		± 1		± 1	μA
I _{oz}	High Impedance Output Leakage Current	5.5	V _I = V _{IH} or V _{IL} V _O = V _{CC} or GND			± 0.5		± 5		± 10	μA
I _{CC}	Quiescent Supply Current	5.5	V _I = V _{CC} or GND			4		40		80	μA
I _{OLD}	Dynamic Output Current (note 1, 2)	5.5	V _{OLD} = 1.65 V max					75		50	mA
I _{OHD}			V _{OHD} = 3.85 V min					-75		-50	mA

1) Maximum test duration 2ms, one output loaded at time

2) Incident wave switching is guaranteed on transmission lines with impedances as low as 50Ω

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AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, $R_L = 500 \Omega$, Input $t_r = t_f = 3 \text{ ns}$)

Symbol	Parameter	Test Condition		Value						Unit	
		V_{CC} (V)		$T_A = 25^\circ\text{C}$			$-40 \text{ to } 85^\circ\text{C}$		$-55 \text{ to } 125^\circ\text{C}$		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t_{PLH} , t_{PHL}	Propagation Delay Time	3.3(*)		1.5	5.5	8.5	1.5	9.0	1.5	11.5	ns
		5.0(**)		1.5	4.5	6.5	1.5	7.0	1.5	8.5	
t_{PZL} , t_{PZH}	Output Enable Time	3.3(*)		1.5	7.5	12.0	1.5	13.5	1.5	14.0	ns
		5.0(**)		1.5	5.5	9.0	1.5	9.5	1.5	10.5	
t_{PLZ} , t_{PHZ}	Output Disable Time	3.3(*)		1.5	6.2	12.0	1.5	13.0	1.5	14.0	ns
		5.0(**)		1.5	5.2	9.0	1.5	10.0	1.5	10.5	

(*) Voltage range is $3.3\text{V} \pm 0.3\text{V}$

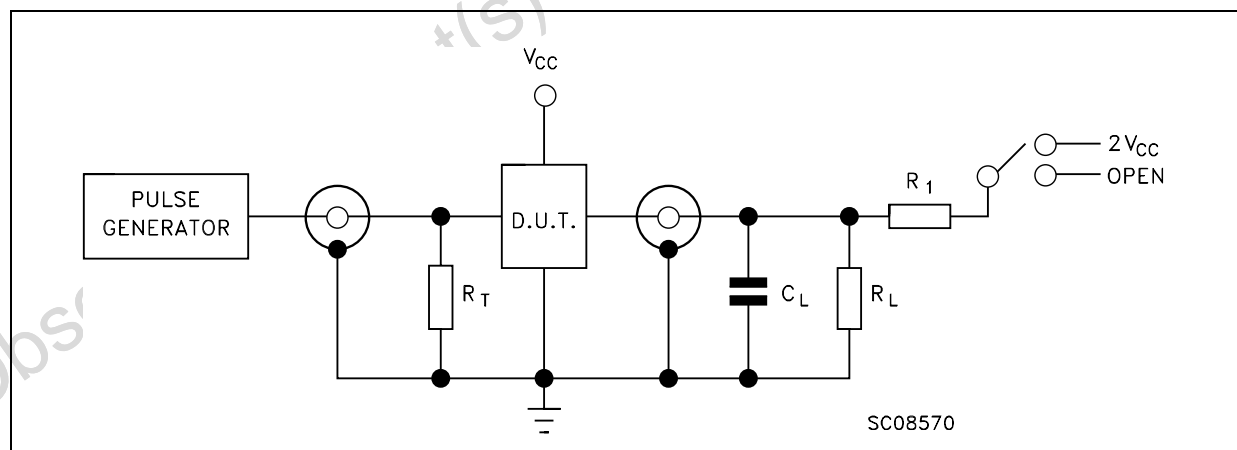
(**) Voltage range is $5.0\text{V} \pm 0.5\text{V}$

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition		Value						Unit	
		V_{CC} (V)		$T_A = 25^\circ\text{C}$			$-40 \text{ to } 85^\circ\text{C}$		$-55 \text{ to } 125^\circ\text{C}$		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
C_{IN}	Input Capacitance	5.0			5						pF
$C_{I/O}$	I/O Capacitance	5.0			10						pF
C_{PD}	Power Dissipation Capacitance (note 1)	5.0	$f_{IN} = 10\text{MHz}$		21						pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(oper)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/16$ (per circuit)

TEST CIRCUIT

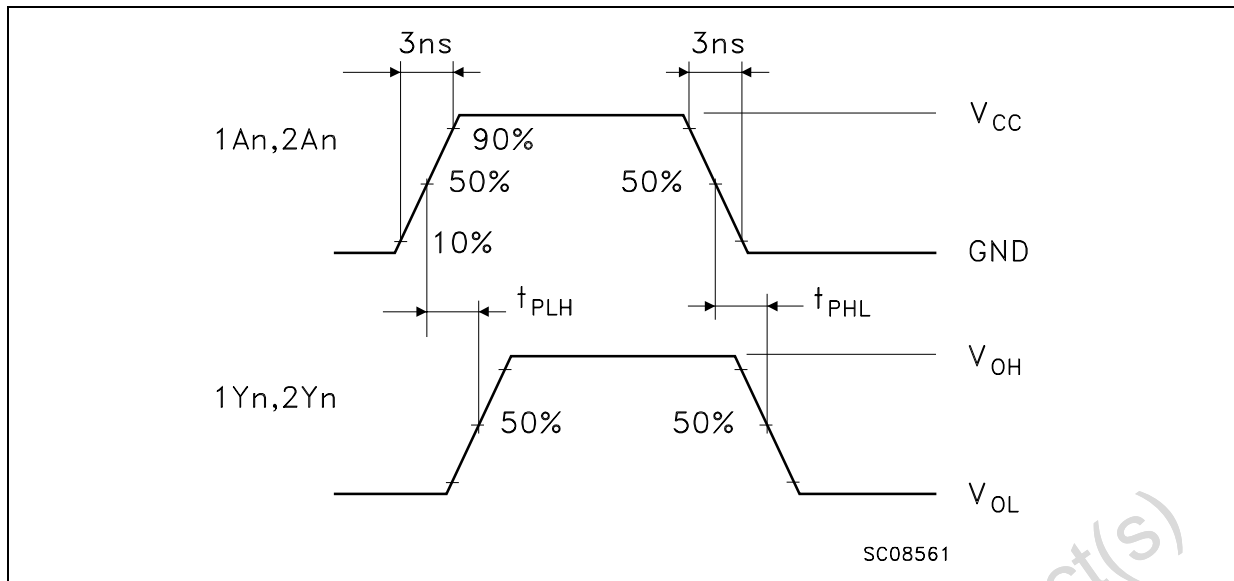
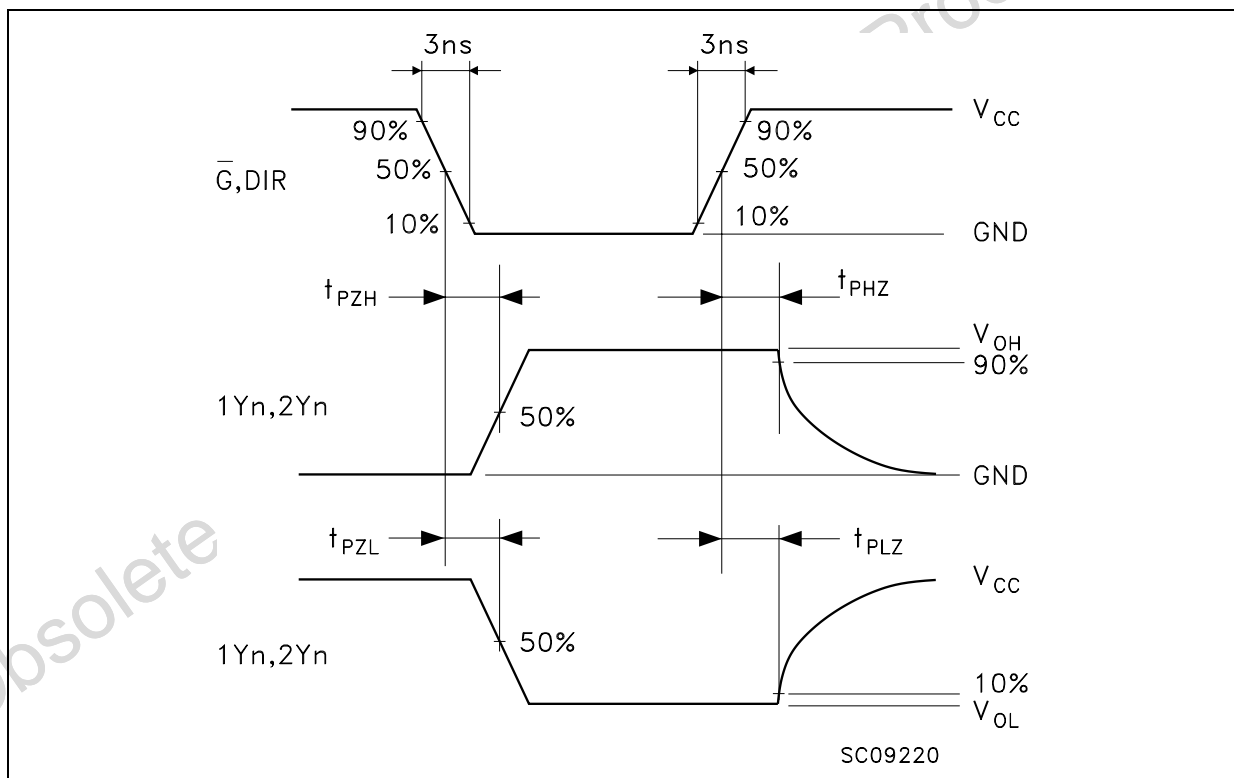


TEST	SWITCH
t_{PLH} , t_{PHL}	Open
t_{PZL} , t_{PLZ}	$2V_{CC}$
t_{PZH} , t_{PHZ}	Open

$C_L = 50 \text{ pF}$ or equivalent (includes jig and probe capacitance)

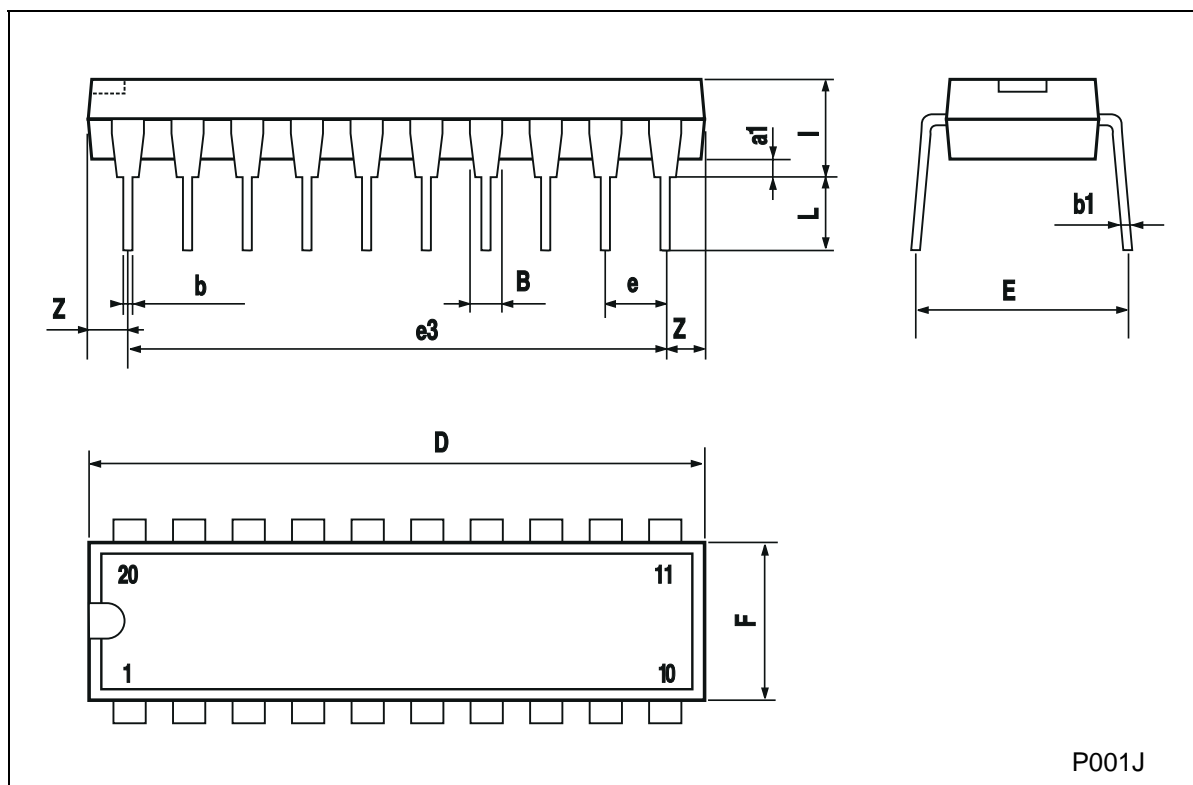
$R_L = R_1 = 500 \Omega$ or equivalent

$R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

WAVEFORM 1: PROPAGATION DELAYS ($f=1\text{MHz}$; 50% duty cycle)**WAVEFORM 2: OUTPUT ENABLE AND DISABLE TIME** ($f=1\text{MHz}$; 50% duty cycle)

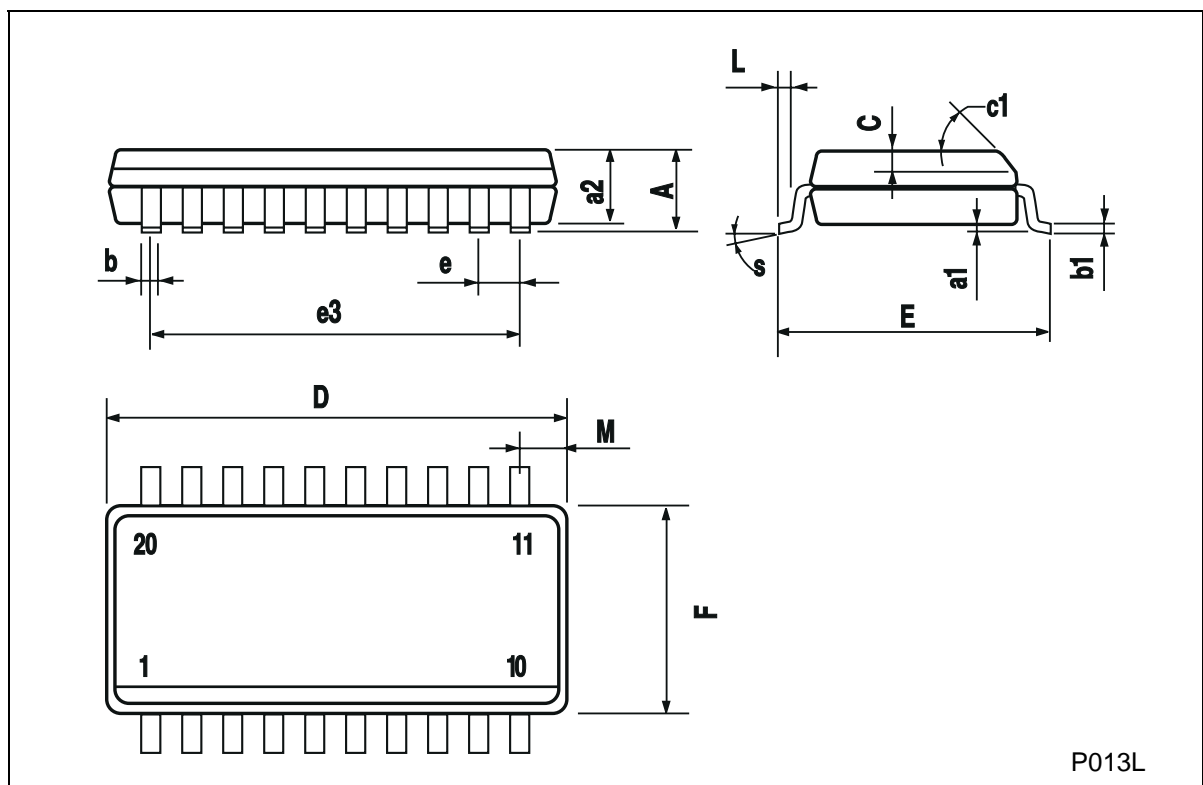
Plastic DIP-20 (0.25) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.254			0.010		
B	1.39		1.65	0.055		0.065
b		0.45			0.018	
b1		0.25			0.010	
D			25.4			1.000
E		8.5			0.335	
e		2.54			0.100	
e3		22.86			0.900	
F			7.1			0.280
I			3.93			0.155
L		3.3			0.130	
Z			1.34			0.053



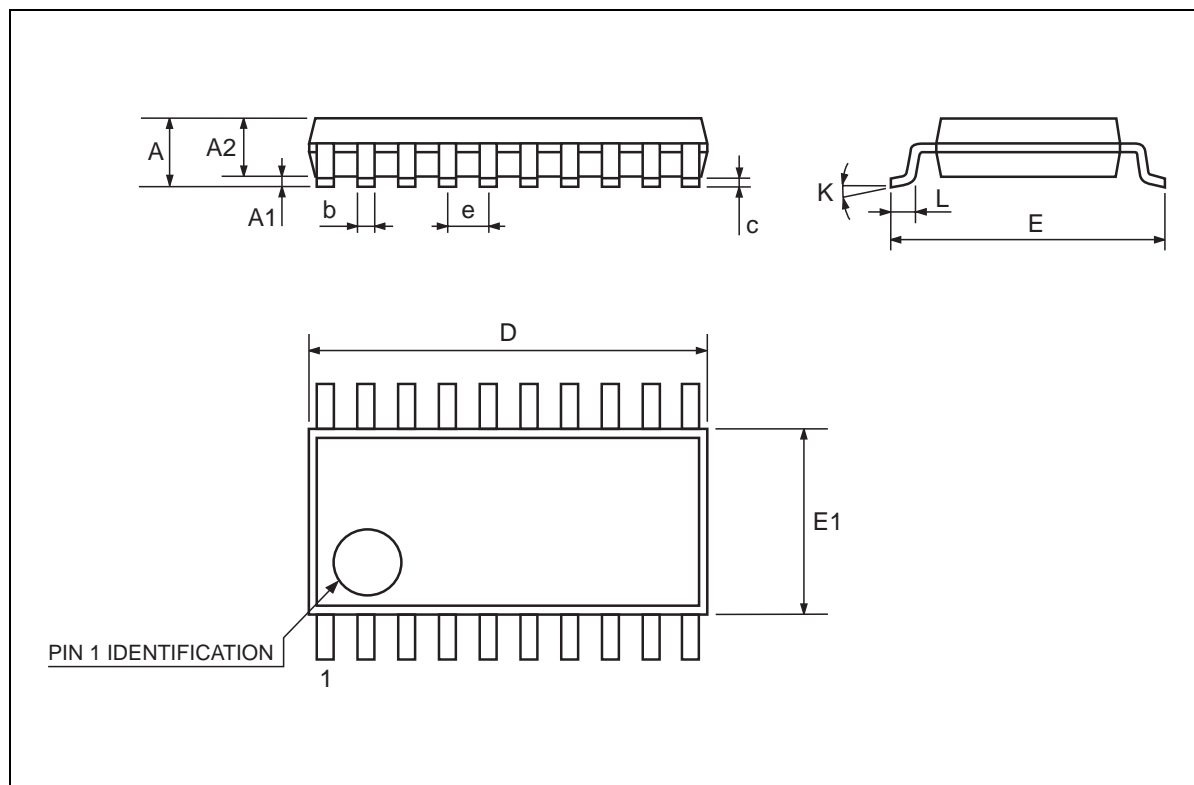
SO-20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			2.65			0.104
a1	0.10		0.20	0.004		0.007
a2			2.45			0.096
b	0.35		0.49	0.013		0.019
b1	0.23		0.32	0.009		0.012
C		0.50			0.020	
c1	45 (typ.)					
D	12.60		13.00	0.496		0.512
E	10.00		10.65	0.393		0.419
e		1.27			0.050	
e3		11.43			0.450	
F	7.40		7.60	0.291		0.299
L	0.50		1.27	0.19		0.050
M			0.75			0.029
S	8 (max.)					



TSSOP20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.1			0.433
A1	0.05	0.10	0.15	0.002	0.004	0.006
A2	0.85	0.9	0.95	0.335	0.354	0.374
b	0.19		0.30	0.0075		0.0118
c	0.09		0.2	0.0035		0.0079
D	6.4	6.5	6.6	0.252	0.256	0.260
E	6.25	6.4	6.5	0.246	0.252	0.256
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°	4°	8°	0°	4°	8°
L	0.50	0.60	0.70	0.020	0.024	0.028



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